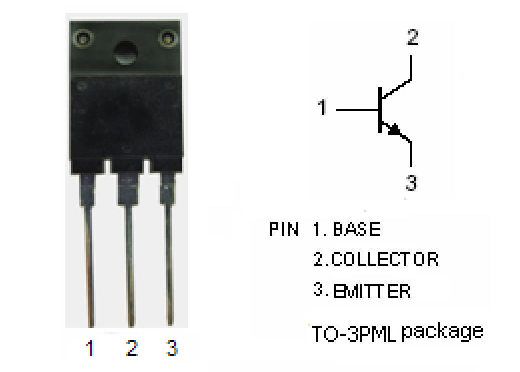
isc Silicon NPN Power Transistor **BU508AF**

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 700V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

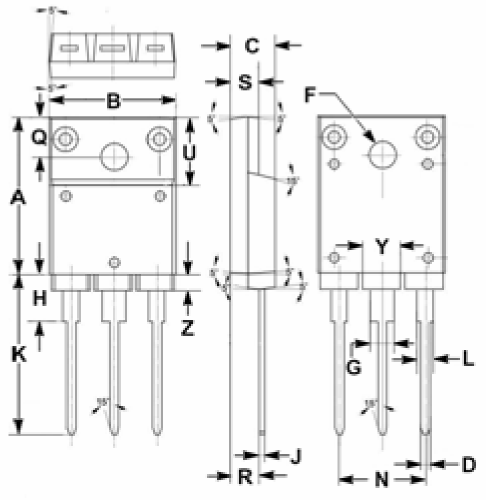
- Designed for use in horizontal deflection circuits of color TV receivers.



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current- Continuous	4	A
I_{BM}	Base Current-Peak	6	A
P_C	Collector Power Dissipation @ T_C=25℃	60	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.5	℃/W



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA ; I_B= 0	700			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4.5A; I_B= 2.0A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 4.5A; I_B= 2.0A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 1500V;I_E= 0			1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5.0V ; I_C= 0			10	mA
h_{FE-1}	DC Current Gain	I_C= 0.1A ; V_{CE}= 5V	6		30	
h_{FE-2}	DC Current Gain	I_C= 4.5A ; V_{CE}= 5V	2.25			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 0.1MHz		125		pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.1A; V_{CE}= 5V; f_{test}= 1.0MHz		7		MHz